

ATTACHMENT A

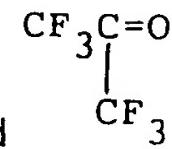
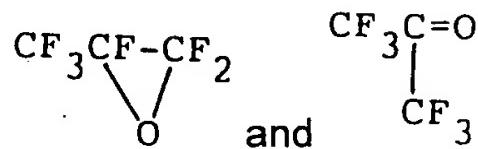
Amendment to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-10. (Canceled)

11. (Currently Amended) A chamber cleaning gas comprising at least one

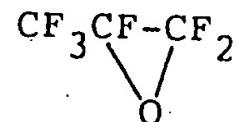
gas selected from the group consisting of CF₃CF=CF₂



wherein the chamber cleaning gas removes reaction byproducts selected from the group consisting of silicon, polysilicon, tungsten, titanium and their oxides, nitrides and carbides attached to the wall of the chamber, and wherein the chamber is a plasma CVD chamber.

12. (Previously Presented) A chamber cleaning gas according to claim 11

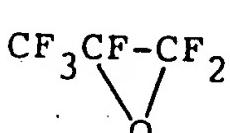
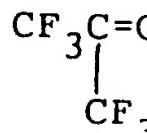
comprising hexafluoropropylene oxide represented by the formula



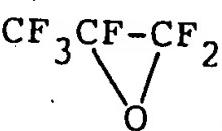
13. (Previously Presented) A chamber cleaning gas according to claim 11 comprising CF₃COCF₃.

14. (Previously Presented) A chamber cleaning gas according to claim 11 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar, H₂, N₂ and O₂.

15. (Currently Amended) A chamber cleaning method comprising the step of treating a plasma CVD chamber of a semiconductor integrated circuit production device with at least one chamber cleaning gas selected from the group consisting of

CF₃CF=CF₂,  and  to remove reaction byproducts selected from the group consisting of silicon, polysilicon, tungsten, titanium and their oxides, nitrides and carbides attached to the wall of the chamber.

16. (Previously Presented) A chamber cleaning method according to claim 15 wherein the chamber cleaning gas is hexafluoropropylene oxide represented by the

formula 

17. (Previously Presented) A chamber cleaning method according to claim 15 wherein the chamber cleaning gas is CF₃COCF₃.

18. (Previously Presented) A chamber cleaning method according to claim 15 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar, H₂, N₂ and O₂.

19. (New) A chamber cleaning method according to claim 15 wherein the chamber cleaning gas is CF₃CF=CF₂.

20. (New) A chamber cleaning method comprising the step of treating a plasma CVD chamber of a semiconductor integrated circuit production device with at least one chamber cleaning gas comprising $\text{CF}_3\text{CF}=\text{CF}_2$ to remove reaction byproducts selected from the group consisting of silicon, polysilicon, tungsten, titanium and their oxides, nitrides and carbides attached to the wall of the chamber.

21. (New) A chamber cleaning gas according to claim 11 wherein the chamber cleaning gas is $\text{CF}_3\text{CF}=\text{CF}_2$.

22. (New) A chamber cleaning gas comprising $\text{CF}_3\text{CF}=\text{CF}_2$ wherein the chamber cleaning gas removes reaction byproducts selected from the group consisting of silicon, polysilicon, tungsten, titanium and their oxides, nitrides and carbides attached to the wall of the chamber, and wherein the chamber is a plasma CVD chamber.